- 1. For the following logic functions:
  - a. Design the PUN and PDN.
  - b. Identify the input combinations that the PUN will be conducting and for each combination determine the PUN resistance,  $r_{PUN}$ , in terms of  $r_{SDP}$  of a single PMOS component.
  - c. Identify the input combinations that the PDN will be conducting and for each combination determine the PDN resistance,  $r_{PDN}$ , in terms of  $r_{DSN}$  of a single NMOS component.
  - d. Using  $k_n = k_p = 4mA/V^2$ ,  $V_{tn} = |V_{tp}| = 0.8V$ , and  $V_{DD} = 3V$ , determine  $r_{DSN}$  and  $r_{SDP}$ .
  - e. For an output capacitance of C=50pF, determine the maximum value of  $T_{PLH}$  and  $T_{PHL}$ .
  - f. Determine the necessary sizes for all the transistors in terms of the the  $(W/L)_{INV}$  that meets timing (n, and p).

$$Y = \overline{A} \cdot \overline{B} \cdot \overline{C} + \overline{D} \cdot \overline{B}$$
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2. A one-bit full adder with carry in/out has three inputs and two outputs.

Inputs:

- A: First coefficient.
- B: Second coefficient.
- $C_{IN}$ : Carry input from previous stage.

Outputs

S: Sum.

COUT: Carry output.

- a. Determine the logic functions for S and  $C_0$  in terms of A, B, and  $C_1$ . Remember, for CMOS design you can only use ANDs, ORs, and NOTs in your logic functions.
- b. Implement each logic function in CMOS.
- c. Determine how many PMOS and NMOS transistors are required.
- d. Using  $k_n = k_p = 20 \text{ mA/V}^2$ ,  $V_{tn} = |V_{tp}| = 0.8 \text{ V}$ , and  $V_{DD} = 2.5 \text{ V}$ , determine  $r_{DSN}$ ,  $r_{SDP}$ .
- e. For an output capacitance of C=40pF, determine the maximum propagation delay for carry output,  $C_{OUT}$ , based on the maximum PUN or PDN resistance.
- f. What would the maximum net delay be for an 8-bit adder and resulting maximum clock rate?

note: If you need to use an inverter to a satisfy the function syntax for the PUN or PDN, just use the inverter symbol in part b and assume (1 PMOS and 1 NMOS) per inverter in part c.